IN THE CLAIM

said at least one test pad

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1	1.	(Canceled)								
;										
·1	2.	(Currently Amended) The method of claim 15 4 wherein said step of								
.2	forming said	interconnect assembly comprises forming said interconnect assembly on a								
3	releasable substrate.									
1	3.	(Currently Amended) The method of claim 15 4 wherein said step of								
2	forming said	interconnect assembly comprises forming at least one test pad in an								
3	interconnect	layer, which at least one test pad can be accessed and electrically								
4	connected o	n opposing sides of said at least one test pad.								
· 1	4.	(Previously Amended) The method of claim 3 wherein said step of								
2	forming at le	ast one test pad forms a test pad having gold on a conductive field metal.								
1	5.	(Previously Amended) The method of claim 3 wherein said step of								
2	forming said	interconnect assembly comprises forming at least one test pad in a								
3	plurality of st	acked interconnect layers, each of which at least one test pad in each								
4	interconnect	layer can be accessed and electrically connected on opposing sides of								

- 6. (Previously Amended) The method of claim 5 wherein said step of 1 2 forming at least one test pad in said plurality of stacked interconnect layers forms at 3 least one test pad in each layer having gold on a conductive field metal.
- 7. (Currently Amended) The method of claim 15 4 where said step of ⁻2 forming said plurality of conductive bumps connected to the terminals of the integrated 3 circuit chip forms a metallic bump making connection to a terminal on said integrated 4 circuit chip and a solder layer disposed on said metallic bump.
- (Previously Amended) The method of claim 7 wherein said step of 8. 1 2 forming said interconnect assembly comprises forming at least one test pad in an 3 interconnect layer, which at least one test pad can be accessed and electrically connected on opposing sides of said test pad, and wherein said step of bonding said 4 5 interconnect assembly to said pre-formed integrated circuit chip flip bonds said solder . 6 layer onto one side of said test pad.
 - 9. (Currently Amended) The method of claim 15 4 where said step of 2 passivating said bonded interconnect assembly and said pre-formed integrated circuit 3 chip into said integral structure to provide said electronic package comprises underfilling 4 said pre-formed integrated circuit chip with an insulating material to remove all voids 5 between said pre-formed prepared integrated circuit chip and said interconnect 6 assembly.

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- 10. (Currently Amended) The method of claim <u>15</u> 1 where said step of passivating said bonded interconnect assembly and said pre-formed integrated circuit chip into said integral structure to provide said electronic package comprises potting said interconnect assembly and said pre-formed integrated circuit chip into an integral package.
- 1 11. (Currently Amended) The method of claim 9 where said step of
 2 passivating said bonded interconnect assembly and said pre-formed integrated circuit
 3 chip into said integral structure to provide said electronic package comprises potting
 4 said interconnect assembly and said pre-formed integrated circuit chip into an integral
 5 package.

1 12. (Previously canceled)

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- 1 13. (Previously Amended) The method of claim 10 further comprising a step 2 of accessing said pre-formed integrated circuit chip through electrical connection to at 3 least one test pad through a surface thereof opposing said surface of said at least one 4 test pad contacting a terminal of said pre-formed integrated circuit chip to test said pre-5 formed integrated circuit chip.
- 1 14. (Currently Amended) The method of claim 10 further comprising a plurality of interconnect assembly and pre-formed integrated circuit chips wherein said

- 3 interconnect assembly and pre-formed integrated circuit chips are bonded together to
- 4 form a corresponding plurality of electronic packages and further comprising the step of
- 5 releasing said plurality of electronic packages from each other.
- 1 15.(Currently Amended) A method of preparing a pre-formed integrated circuit 2 chip for encapsulation in an electronic package, comprising the steps of:
- forming an interconnect assembly separately from said pre-formed integrated
- 4 circuit chip;
- 5 forming a plurality of conductive bumps connected to the terminals of the pre-
- 6 formed integrated circuit chip;
- bonding said interconnect assembly to said pre-formed integrated circuit chip;
- 8 passivating said bonded interconnect assembly and said pre-formed integrated
- 9 circuit chip into an integral structure; and
- thinning said pre-formed integrated circuit chip to provide said electronic
- 11 <u>package</u>,
- the The method of claim 1 further comprising a plurality of interconnect
- assembly and pre-formed integrated circuit chips wherein said plurality of interconnect
- 14 assembly and pre-formed integrated circuit chips are bonded together to form a
- 15 corresponding plurality of electronic packages and further comprising the step of testing
- said interconnect assembly and bonding a tested interconnect assembly in said step of
- 17 bonding said interconnect assembly to said pre-formed integrated circuit chip only if
- 18 said interconnect assembly tested good.

- 1 16. (Previously Amended) The method of claim 15 where said step of forming 2 said plurality of interconnect assemblies comprises forming said interconnect 3 assemblies simultaneously in a wafer and where said plurality of pre-formed integrated
- 4 circuit chips are individually bump bonded to successfully tested ones of said
- · 5 interconnect assemblies.
- 1 17 33. (Canceled)
- 1 34. (Currently Amended) The method of claim 43 33 wherein the at least one test pad has gold on a conductive field metal.
- 1 35. (Currently Amended) The method of claim 43 33 where said step of
 2 forming said plurality of conductive bumps connected to the terminals of the integrated
 3 circuit chip forms a metallic bump making connection to a terminal on said integrated
 4 circuit chip and a solder layer disposed on said metallic bump.
 - 1 36. The method of claim 35 wherein said step of forming said interconnect
 2 assembly comprises forming at least one test pad in an interconnect layer, which at
 3 least one test pad can be accessed and electrically connected on opposing sides of
 4 said test pad, and wherein said step of bonding said interconnect assembly to said pre5 formed integrated circuit chip flip bonds said solder layer onto one side of said test pad.

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- 1 40. (Currently Amended) The method of claim 43 39 further comprising the step thinning said pre-formed integrated circuit chip.
- 1 41. (Currently Amended) The method of claim 43 39 further comprising a step
 2 of accessing said pre-formed integrated circuit chip through electrical connection to at
 3 least one test pad through a surface thereof opposing said surface of said at least one
 4 test pad contacting a terminal of said pre-formed integrated circuit chip to test said pre5 formed integrated circuit chip.
- 1 42. (Canceled)
- 1 43. (Currently Amended) <u>A method of preparing a pre-formed integrated</u>
 2 <u>circuit chip for encapsulation in an electronic package, comprising the steps of:</u>
- forming an interconnect assembly separately from said pre-formed integrated circuit chip, said forming an interconnect assembly including the step of:
- forming at least one test pad in a plurality of stacked interconnect layers,

 each of which at least one test pad in each interconnect layer can be

 accessed and electrically connected on opposing sides of said at least

 one test pad;

•	forming a	plurality o	f conductive	<u>bumps</u>	connected	to the	terminals	of the	pre-
		_			- .				<u>-</u> .
<u>forme</u>	d integrate	d circuit cl	nip;						

bonding said interconnect assembly to said pre-formed integrated circuit chip;

passivating said bonded interconnect assembly and said pre-formed integrated circuit chip into an integral structure to provide said electronic package,

where said step of passivating said bonded interconnect assembly and said preformed integrated circuit chip into said integral structure to provide said electronic

package comprises underfilling said pre-formed integrated circuit chip with an insulating
material to remove all voids between said pre-formed integrated circuit chip and said
interconnect assembly,

where said step of passivating said bonded interconnect assembly and said preformed integrated circuit chip into said integral structure to provide an electronic

package comprises potting said interconnect assembly and said pre-formed integrated

circuit chip into said integral package,

The the method of claim 39 further comprising a plurality of interconnect assembly and pre-formed integrated circuit chips wherein said plurality of interconnect assembly and pre-formed integrated circuit chips are bonded together to form a corresponding plurality of electronic packages and further comprising the step of testing said interconnect assembly and bonding a tested interconnect assembly in said step of bonding said interconnect assembly to said pre-formed integrated circuit chip only if said interconnect assembly tested good.

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<u>and</u>

- 1 44. The method of claim 43 where said step of forming said plurality of
- 2 interconnect assemblies comprises forming said interconnect assemblies
- · 3 simultaneously in a wafer and where said plurality of pre-formed integrated circuit chips
- 4 are individually bump bonded to successfully tested ones of said interconnect
- 5 assemblies.